

AMENDMENT

Please amend the claims as follows:

1. (amended herein) A treatment system for the treatment of effluent gases from a semiconductor device manufacturing process, the treatment system comprising:

(a) an abatement system comprising:

- i) a burn/wet scrubber for receiving a flow of effluent gas containing a toxic constituent and for producing a flow of treated gas and a flow of waste~~[[-]]~~water containing the toxic constituent; and
- ii) a localized wastewater treatment unit comprising an ion exchange filter selected to reduce the concentration of said toxic constituent, for receiving said flow of wastewater containing the toxic constituent, [[

(b) a local waste water treatment unit associated with the burn/wet scrubber for receiving the flow of wastewater containing the toxic constituent]] and for producing a flow of locally treated wastewater from which the toxic constituent has been abated.

2. (amended herein) The treatment system of claim 1 further comprising a plurality of burn/wet scrubbers in fluid communication with ~~a single local~~ said localized wastewater treatment unit.

3. (cancelled herein)

4. (cancelled herein)

5. (amended herein) The treatment system of claim 1 ~~and including~~ additionally comprising a central wastewater treatment facility for receiving and further treating the locally treated wastewater.

6. (amended herein) The treatment system of claim ~~[[1]]~~5 further comprising a plurality of burn/wet scrubbers and a plurality of localized wastewater treatment units wherein each said burn/wet scrubbers is in fluid communication with a ~~corresponding~~ localized wastewater treatment unit, and each said localized wastewater treatment unit is in fluid communication with the central wastewater treatment facility.

7-14. (withdrawn)

15. (new) The treatment system of claim 1 wherein said ion exchange filter is selected to reduce the concentration of arsenic and germanium.

16. (new) The treatment system of claim 15 wherein said ion exchange filter is selected to reduce the concentration of arsenic to a concentration below 50 ppb.

17. (new) The treatment system of claim 15 wherein said ion exchange filter is selected to reduce the concentration of germanium to a concentration below 50 ppb.